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IEEE RTP 2007 Conference

Tuesday, October 2, 2007

9:00AM-5:00pm

Workshop:
Low thermal budget processing for organic and hybrid Si-plastic large area electronics 327

Wednesday, October 3, 2007

PLENARY SESSION
Chairs: J. Gelpey, Mattson Technology, K. Suguro, Toshiba

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Conference Opening

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B. Mizuno, Y. Sasaki
Ultimate Junction Technologies Inc., Osaka, Japan

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Salvatore Coffa
ST Microelectronics, Catania, Italy

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Applied Materials, Sunnyvale, CA

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AMD Saxony, Dresden, Germany

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F. Tumisto, K. Kuitunen, Helsinky University of Technology, Finland

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Research Center Rossendorf, Dresden, Germany
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T. Gebel, W. Hentsch, R. Fendler, FHR GmbH, Ottendorf-Okrilla, Germany
T. Lüthge, Degussa GmbH, Marl, Germany
A. Satta, IMEC, Leuven, Belgium
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B. Lojek, ATMEL, Colorado Springs

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Hungarian Academy of Sciences, Budapest, Hungary
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IEEE RTP2007 Achievement Award Ceremony

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V. Raineri[2], E. Napolitani[3], A. Carnera[3]
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[2]CNR-IMM, Catania, Italy
[3]MATIS - CNR-INFM and Dipartimento di Fisica, Università di Padova, Padova, Italy

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IMEC, Leuven, Belgium
J.A. Kittl, Assignee from Texas Instruments at IMEC
K. Verheyden, K. Vanormelingen, ASM Belgium, IMEC
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[1] CNR-IMM, Catania, Italy
[2]Dipartimento di Fisica e Astronomia, Università di Catania, Catania,Italy
[3]Dipartimento di Scienze Chimiche, Università di Catania, Catania, Italy

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[2] ASM France, Grenoble, France
[3] ASM Belgium, Leuven, Belgium
[4] IMEC, Leuven, Belgium

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[1] ASM Belgium, Leuven, Belgium
[2] ASM France, Grenoble, France
[3] ASM America, Phoenix, AZ
[4] IMEC, Leuven, Belgium
[5]ASM Europe B.V., Almere, The Netherland

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[1] CNR-IMM, Catania, Italy
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[3]Dipartimento di Fisica e Astronomia, Università di Catania, Catania,Italy
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[1] Mattson Thermal Products, Germany
[2] Mattson Technology Canada, Canada
[3] IHP, Frankfurt/Oder, Germany
[4]LAAS/CNRS, Toulouse, France
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[1] Applied Materials, Sunnyvale, CA
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[3] Applied Materials Korea, Kyonggi-do, Korea

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[1] Ultratech Inc., San Jose, CA
[2] Texas Instruments, Dallas, TX

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[1] Coherent GmbH, Goettingen, Germany
[2] Coherent Inc., Santa Clara, CA

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[1] IMEC, Leuven, Belgium
[2] Texas Instruments assignee at IMEC, Leuven, Belgium
[3] Applied Materials, Sunnyvale, CA
[4] Applied Materials Belgium, Leuven, Belgium

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[1] Keio University, Kanagawa, Japan
[2]SEN Corporation, SEN Corporation, Tokyo, Japan
[3]Sumitomo Heavy Industries Ltd., Kanagawa, Japan

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[1]Fujitsu Ltd. and [2]Fujitsu Laboratories Ltd., Tokyo, Japan

Adjourn